



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AJT150** is Designed for

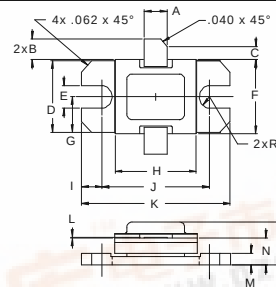
FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.57 °C/W

PACKAGE STYLE .400 2L FLG (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.135 / 3.43	.145 / 3.68
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.376 / 9.55	.396 / 10.06
E	.110 / 2.79	.130 / 3.30
F	.395 / 10.03	.407 / 10.34
G	.193 / 4.90	
H	.490 / 12.45	.510 / 12.95
I	.100 / 2.54	
J	.690 / 17.53	.710 / 18.03
K	.890 / 22.61	.910 / 23.11
L	.003 / 0.08	.006 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10548

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50\text{ mA}$	35			V
BV_{CER}	$I_C = 50\text{ mA}$ $R_{BE} = 10\text{ }\Omega$	60			V
BV_{EBO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_{BE} = 50\text{ V}$			5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		100	---
P_G η_C	$V_{CC} = 50\text{ V}$ $P_{OUT} = 150\text{ W}$ $f = 960 - 1215\text{ MHz}$	7.5 40			dB %

